

## **Description**

The HNTR3C21NZT1G uses advanced trench technology

to provide excellent  $R_{\text{DS}(\text{ON})}$ , low gate charge and

operation with gate voltages as low as 2.5V. This

device is suitable for use as a Battery protection

or in other Switching application.

#### **General Features**

 $V_{DS} = 20V I_{D} = 6.5A$ 

 $R_{DS(ON)}$  < 22m $\Omega$  @  $V_{GS}$ =4. 5V

ESD=2500HBM

### **Application**

Battery protection

Load switch

Uninterruptible power supply

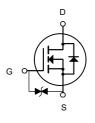
### **Package Marking and Ordering Information**

Product ID	Pack	Marking	Qty(PCS)	
HNTR3C21NZT1G SOT-23-3L(SOT-23-3)		AGBV 1N	3000	

## Absolute Maximum Ratings (T<sub>A</sub>=25<sup>°</sup>C unless otherwise noted)

Symbol	Parameter	Limit	Unit	
VDS	Drain-Source Voltage	20	V	
Vgs	Gate-Source Voltage	±12	V	
ID	Drain Current-Continuous	6.5	А	
Ірм	Drain Current-Pulsed (Note 1)	30	А	
PD	Maximum Power Dissipation	1.4	W	
Тл,Тятв	Operating Junction and Storage Temperature Range	-55 To 150	°C	
Rеја	Thermal Resistance,Junction-to-Ambient (Note 2)	89	°C/W	





N-Channel MOSFET



### N-Channel Enhancement Mode MOSFET

# Electrical Characteristics (T<sub>A</sub>=25°Cunless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V I <sub>D</sub> =250µA	20		-	V
Zero Gate Voltage Drain Current	IDSS	V <sub>DS</sub> =20V,V <sub>GS</sub> =0V	-	-	1	μA
Gate-Body Leakage Current	Igss	V <sub>GS</sub> =±10V,V <sub>DS</sub> =0V	-	-	±10	μA
Gate Threshold Voltage	VGS(th)	V <sub>DS</sub> =V <sub>GS</sub> ,I <sub>D</sub> =250μA	0.45	0.7	1.0	V
		V <sub>GS</sub> =4.5V, I <sub>D</sub> =6.5A	-	14	22	mΩ
Drain-Source On-State Resistance	RDS(ON)	V <sub>GS</sub> =2.5V, I <sub>D</sub> =5.5A	-	17	26	mΩ
		V <sub>GS</sub> =1.8V, I <sub>D</sub> =5A	-	28	40	mΩ
Forward Transconductance	grs	V <sub>DS</sub> =5V,I <sub>D</sub> =6.5A	8	-	-	S
Input Capacitance	C <sub>lss</sub>		-	660	-	PF
Output Capacitance	Coss	$V_{DS}$ =10V, $V_{GS}$ =0V, F=1.0MHz	-	160	-	PF
Reverse Transfer Capacitance	C <sub>rss</sub>		-	87	-	PF
Turn-on Delay Time	Turn-on Delay Time t <sub>d(on)</sub>		-	0.5	-	nS
Turn-on Rise Time	t <sub>r</sub>	$V_{DD}$ =10V, $R_L$ =1. $5\Omega$ $V_{GS}$ =5V, $R_{GEN}$ =3 $\Omega$	-	1	-	nS
Turn-Off Delay Time	t <sub>d(off)</sub>		-	12	-	nS
Turn-Off Fall Time	t <sub>f</sub>		-	4	-	nS
Total Gate Charge	Total Gate Charge Q <sub>g</sub>		-	8	-	nC
Gate-Source Charge	$Q_{gs}$	$V_{DS}$ =10V, $I_{D}$ =6.5A, $V_{GS}$ =4.5V	-	2.5	-	nC
Gate-Drain Charge	$Q_{gd}$		-	3	-	nC
Diode Forward Voltage (Note 3)	VsD	V <sub>GS</sub> =0V,I <sub>S</sub> =6.5A	-	-	1.2	V
Diode Forward Current (Note 2)	Is		-	-	6.5	А

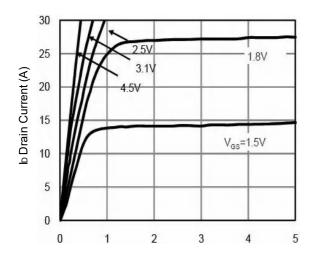
### Notes:

Repetitive Rating: Pulse width limited by maximum junction temperature. Surface

Mounted on FR4 Board, t ≤ 10 sec.
Pulse Test: Pulse Width ≤ 300µs, Duty Cycle ≤ 2%.
Guaranteed by design, not subject to production



### **Typical Characteristics**



**Fig.1 Typical Output Characteristics** 

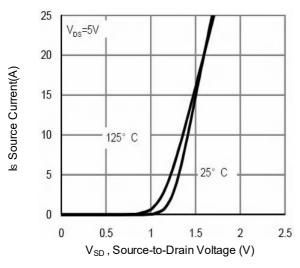


Fig.3 Forward Characteristics of Reverse

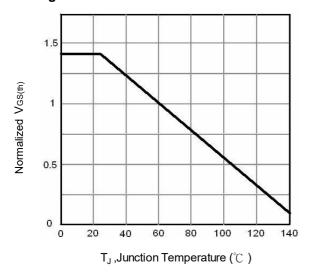


Fig.5 Normalized V<sub>GS(th)</sub> vs. T<sub>J</sub>

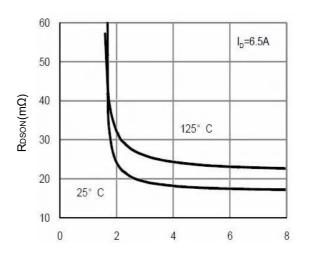


Fig.2 On-Resistance vs. Gate-Source

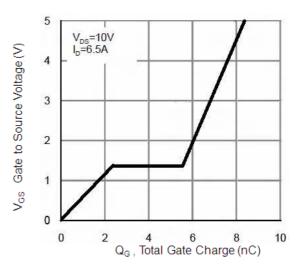


Fig.4 Gate-Charge Characteristics

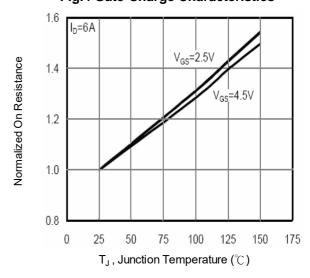
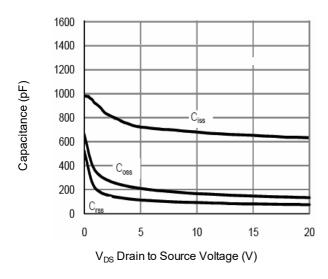


Fig.6 Normalized R<sub>DSON</sub> vs. T<sub>J</sub>



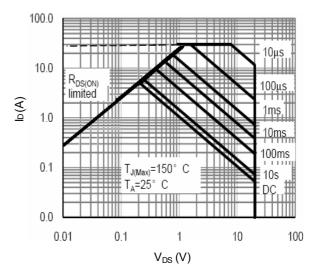
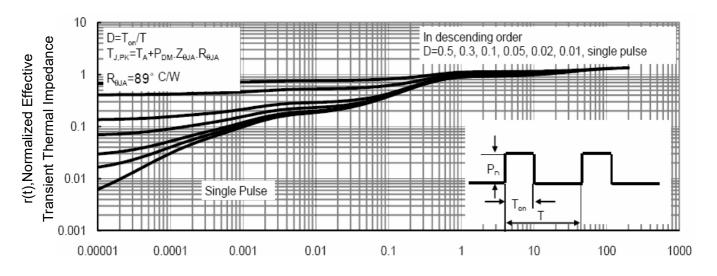
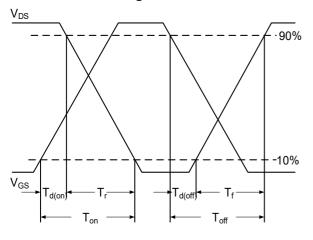


Fig.7 Capacitance

Fig.8 Safe Operating Area



Square Wave Pluse Duration(sec)
Fig.9 Normalized Maximum Transient Thermal Impedance



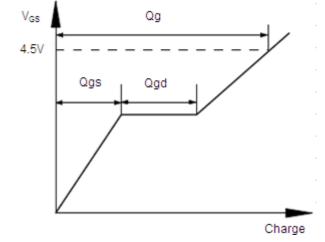
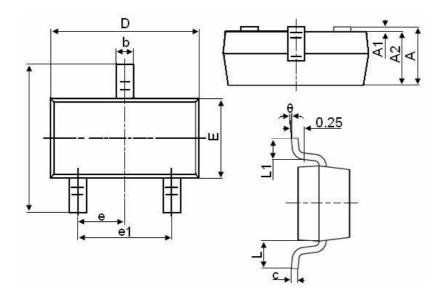


Fig.10 Switching Time Waveform

Fig.11 Gate Charge Waveform

# N-Channel Enhancement Mode MOSFET

# SOT-23-3L(SOT-23-3) Package Information



Symbol	Dimensions in Millimeters			
	MIN.	MAX.		
А	1.050	1.250		
A1	0.000	0.100		
A2	1.050	1.150		
b	0.300	0.500		
С	0.100	0.200		
D	2.800	3.000		
E	1.500	1.700		
E1	2.650	2.950		
е		0.950TYP		
e1	1.800	2.000		
L		0.550REF		
L1	0.300	0.600		
θ	0°	8°		



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